

# MBT2222ADW1, NSVBT2222ADW1

## General Purpose Transistor

### NPN Silicon

#### Features

- Moisture Sensitivity Level: 1
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	40	Vdc
Collector–Base Voltage	$V_{CBO}$	75	Vdc
Emitter–Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current – Continuous	$I_C$	600	mAdc
Electrostatic Discharge	ESD	HBM Class 2 MM Class B	

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Package Dissipation (Note 1), $T_A = 25^\circ\text{C}$	$P_D$	150	mW
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

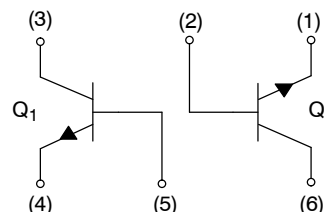
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.



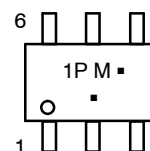
ON Semiconductor®

<http://onsemi.com>



SC-88/SC70-6/SOT-363  
CASE 419B  
STYLE 1

#### MARKING DIAGRAM



1P = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
MBT2222ADW1T1G	SOT-363 (Pb-Free)	3000 / Tape & Reel
NSVBT2222ADW1T1G	SOT-363 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MBT2222ADW1, NSVB2222ADW1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	40	–	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	75	–	Vdc
Emitter–Base Breakdown Voltage, ( $I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	6.0	–	Vdc
Collector Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $V_{EB(off)} = 3.0\text{ Vdc}$ )	$I_{CEX}$	–	10	nAdc
Collector Cutoff Current ( $V_{CB} = 60\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 60\text{ Vdc}$ , $I_E = 0$ , $T_A = 125^\circ\text{C}$ )	$I_{CBO}$	– –	0.01 10	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = 3.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	100	nAdc
Base Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $V_{EB(off)} = 3.0\text{ Vdc}$ )	$I_{BL}$	–	20	nAdc

## ON CHARACTERISTICS

DC Current Gain ( $I_C = 0.1\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $T_A = -55^\circ\text{C}$ ) ( $I_C = 150\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) (Note 2) ( $I_C = 150\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ ) (Note 2) ( $I_C = 500\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) (Note 2)	$h_{FE}$	35 50 75 35 100 50 40	– – – – 300 – –	–
Collector–Emitter Saturation Voltage (Note 2) ( $I_C = 150\text{ mA}$ , $I_B = 15\text{ mA}$ ) ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )	$V_{CE(sat)}$	– –	0.3 1.0	Vdc
Base–Emitter Saturation Voltage (Note 2) ( $I_C = 150\text{ mA}$ , $I_B = 15\text{ mA}$ ) ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )	$V_{BE(sat)}$	0.6 –	1.2 2.0	Vdc

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (Note 3) ( $I_C = 20\text{ mA}$ , $V_{CE} = 20\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	300	–	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	–	8.0	pF
Input Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	–	25	pF
Input Impedance ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{ie}$	2.0 0.25	8.0 1.25	k $\Omega$
Voltage Feedback Ratio ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{re}$	– –	8.0 4.0	$\times 10^{-4}$
Small–Signal Current Gain ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	50 75	300 375	–
Output Admittance ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$	5.0 25	35 200	$\mu\text{mhos}$
Collector Base Time Constant ( $I_E = 20\text{ mA}$ , $V_{CB} = 20\text{ Vdc}$ , $f = 31.8\text{ MHz}$ )	$r_b$ , $C_c$	–	150	ps
Noise Figure ( $I_C = 100\text{ }\mu\text{A}$ , $V_{CE} = 10\text{ Vdc}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	NF	–	4.0	dB

## SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 30\text{ Vdc}$ , $V_{BE(off)} = -0.5\text{ Vdc}$ , $I_C = 150\text{ mA}$ , $I_{B1} = 15\text{ mA}$ )	$t_d$	–	10	ns
Rise Time		$t_r$	–	25	
Storage Time	$(V_{CC} = 30\text{ Vdc}$ , $I_C = 150\text{ mA}$ , $I_{B1} = I_{B2} = 15\text{ mA}$ )	$t_s$	–	225	ns
Fall Time		$t_f$	–	60	

2. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

3.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

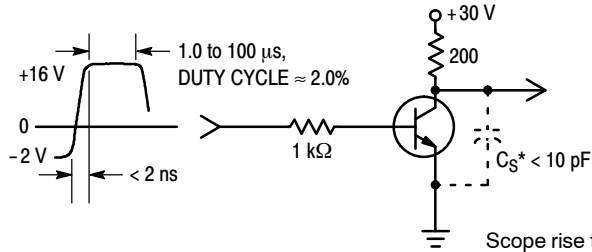


Figure 1. Turn-On Time

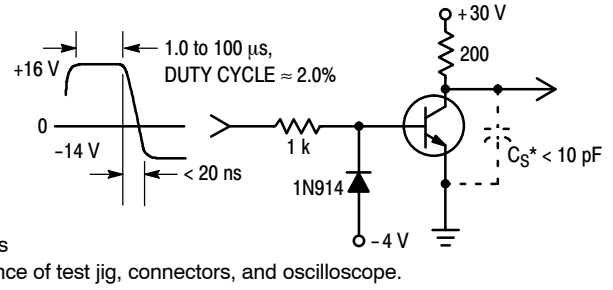


Figure 2. Turn-Off Time

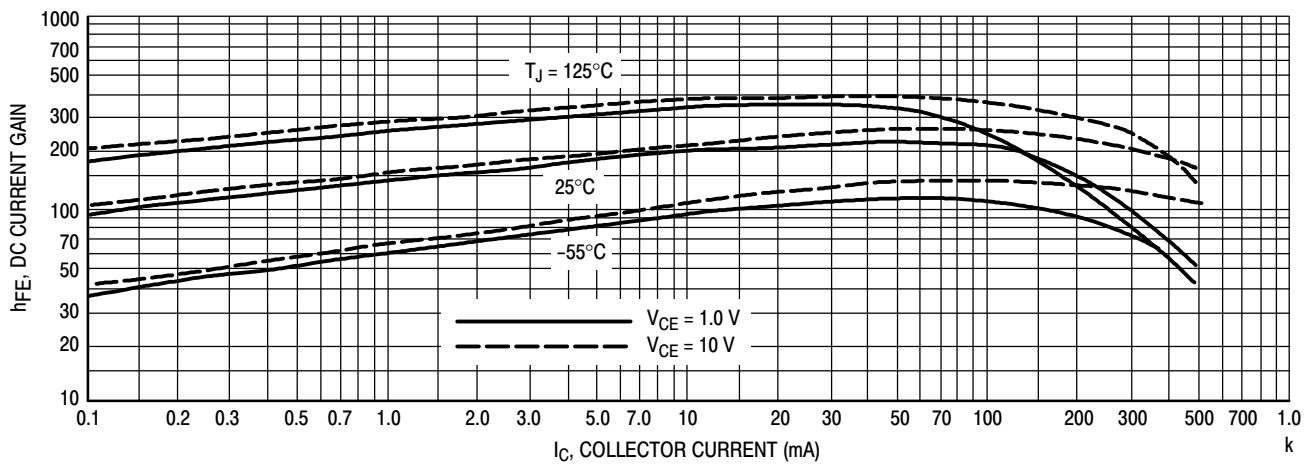


Figure 3. DC Current Gain

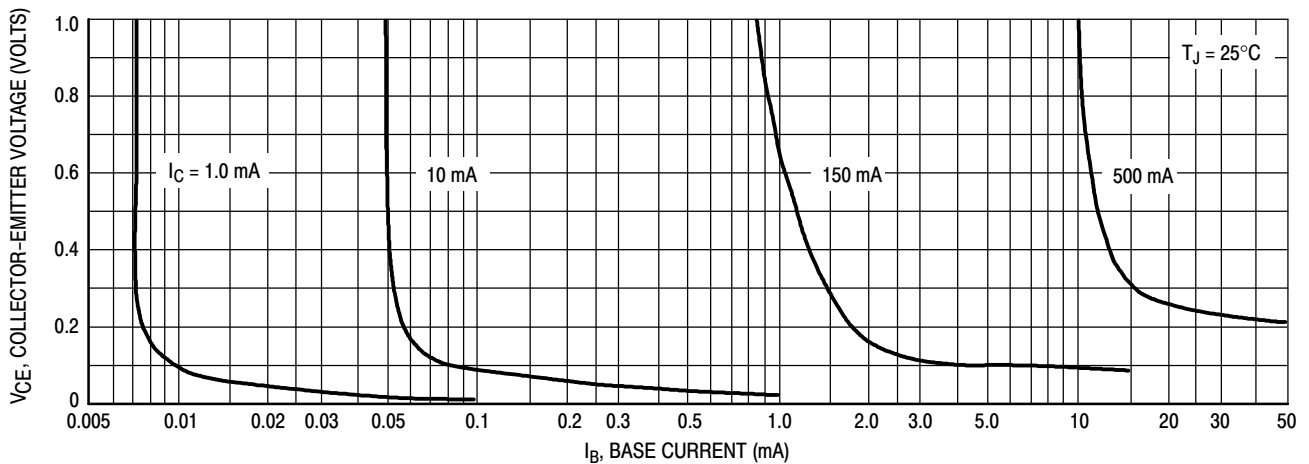


Figure 4. Collector Saturation Region

# MBT2222ADW1, NSVBT2222ADW1

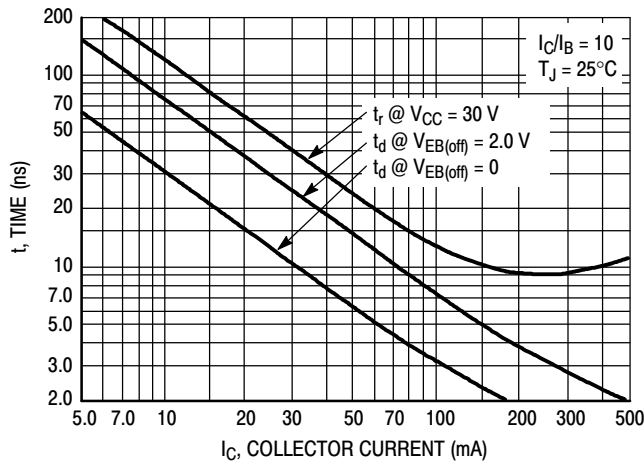


Figure 5. Turn-On Time

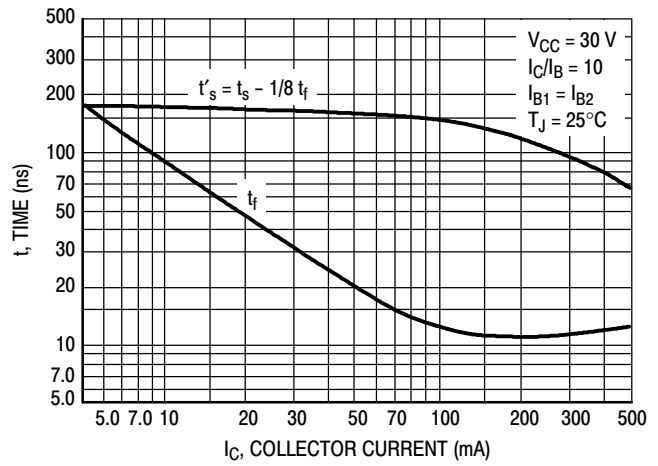


Figure 6. Turn-Off Time

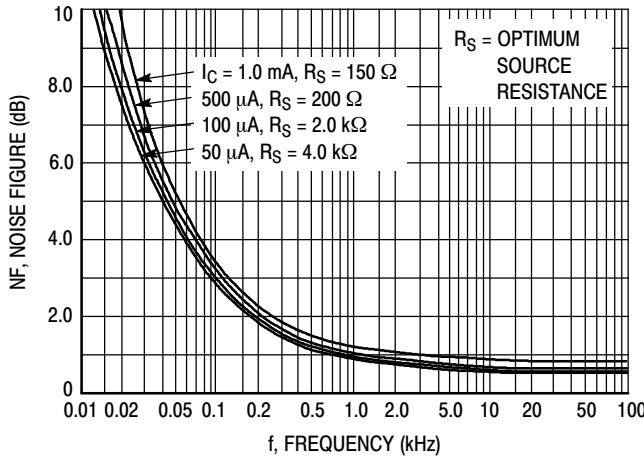


Figure 7. Frequency Effects

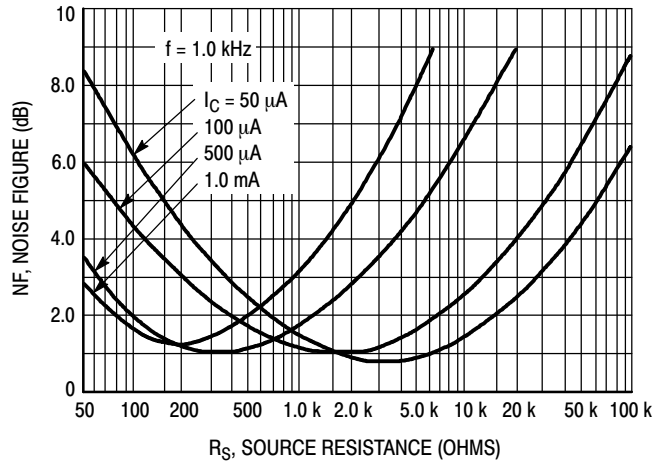


Figure 8. Source Resistance Effects

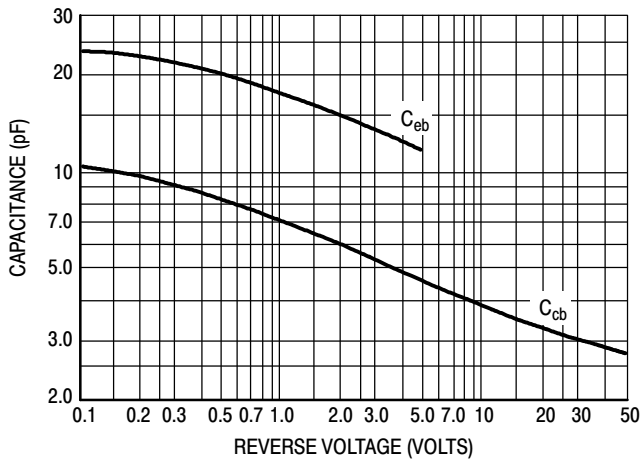


Figure 9. Capacitances

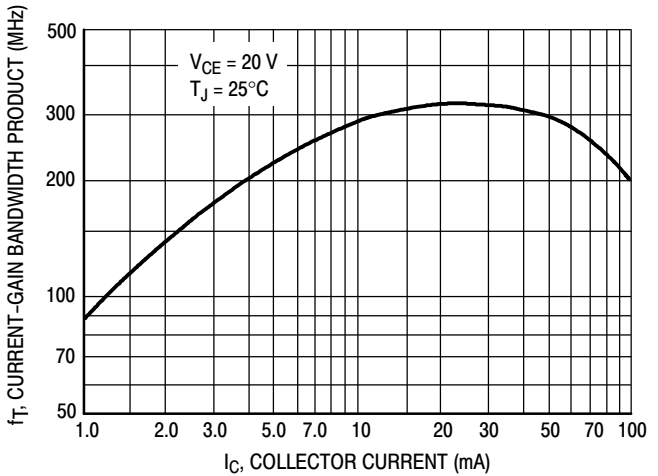


Figure 10. Current-Gain Bandwidth Product

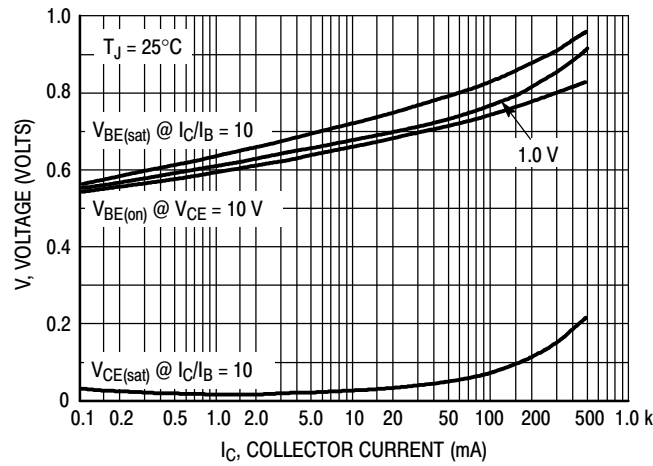


Figure 11. "On" Voltages

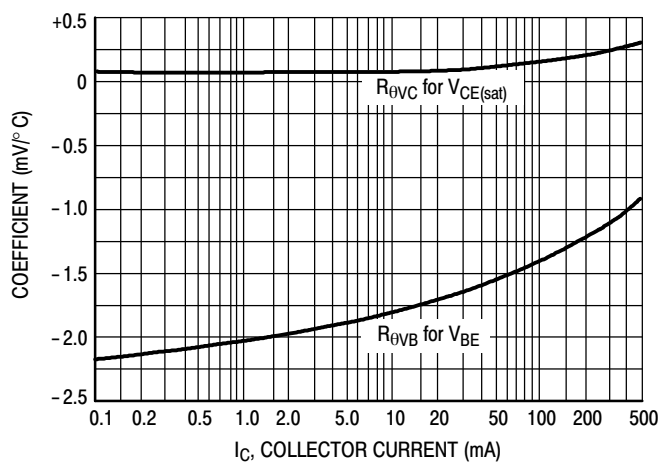


Figure 12. Temperature Coefficients

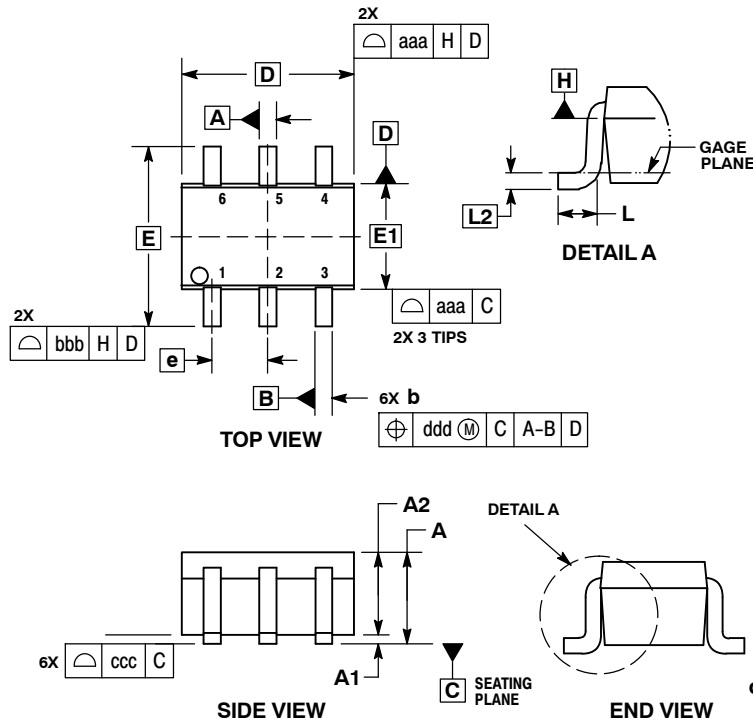
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## PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02

ISSUE Y



### NOTES:

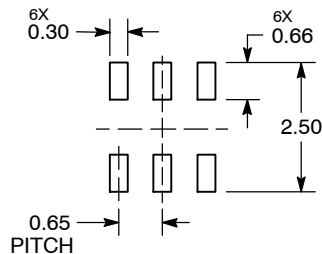
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

### STYLE 1:

1. PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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